

Form PTO-1449
(Rev. 8-93)U.S. Department of Commerce
Patent and Trademark Office

Attorney Docket No. 0756-958

Serial No. 08/183,800

INFORMATION DISCLOSURE STATEMENT

(Use several sheets if necessary)

Applicant: Shunpei YAMAZAKI

Filing Date: 01/21/94

Group: 2508

U.S. PATENT DOCUMENTS

Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date (if appropriate)
SWC	4,266,986	05/12/81	BENTON et al.			11/29/79
	5,210,050	05/11/93	YAMAZAKI et al.			10/11/91
	5,272,361	12/21/93	YAMAZAKI, Shunpei			11/01/91
	4,959,700	09/25/90	YAMAZAKI, Shunpei			02/03/88
	5,306,651	04/26/94	MASUMO et al.			05/10/91
	5,278,093	01/11/94	YONEHARA, Takao			07/29/92
	5,091,334	02/25/92	YAMAZAKI et al.			03/05/90
	4,969,031	11/06/90	KOBAYASHI et al.			02/03/83
	4,897,360	01/30/90	GUCKEL et al.			12/09/87
SWC	4,860,069	08/22/89	YAMAZAKI, Shunpei			10/02/87

FOREIGN PATENT DOCUMENTS

	Document Number	Date	Country	Class	Subclass	Translation Yes No	
SWC	0 178 447	04/23/86	Europe			X	
SWC	161 555 A	10/21/85	EP			X	
SWC	2 103925	04/17/90	Japan			ABS	

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

SWC	WOLF et al., "Silicon Processing For The VLSI Era", Vol I, Lattice Press, Sunset Beach, California, pp. 19-21.
SWC	SAMESHIMA et al., "XeCl Excimer Laser Annealing Used to Fabricate Poly-Si TFT's", Japanese Journal of Applied Physics, Vol. 28, No. 10, October 1989, pp. 1789-1793.
SWC	IWAMATSU et al., "Silicon-On-Sapphire M.O.S.F.E.T.S. Fabricated By Back-Surface Laser-Anneal Technology, Electronics Letters, Vol. 15, #25, pp. 827-828, December 1979.
SWC	SERA et al., "High Performance TFT's Fabricated by XeCl Excimer Laser Annealing of Hydrogenated Amorphous-Silicon Film", IEEE Transactions on Electron Devices, 36(1989), pp. 2868-2872.
SWC	KIANG et al., "Modification of Semiconductor Device Characteristics by Lasers", IBM, 1982, pp. 171-6.
SWC	PRESSLEY, "Excimer Laser Processing of Semiconductors", Lasers & Applications, May 1985, pp. 93-98.

Examiner

CRANE

Date Considered

9/25/98

*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Form PTO-1449
(Rev. 8-83)U.S. Department of Commerce
Patent and Trademark Office

Attorney Docket No. 0756-958

Serial No. 08/183,800

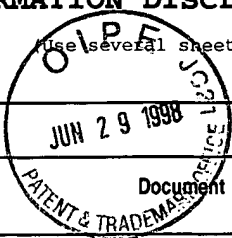
INFORMATION DISCLOSURE STATEMENT

(Use several sheets if necessary)

Applicant: Shunpei YAMAZAKI

Filing Date: 01/21/94

Group: 2508

**U.S. PATENT DOCUMENTS**

Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date (if appropriate)
SWC	4,986,213	01/22/91	YAMAZAKI et al.			09/28/88
	4,891,330	01/02/90	GUHA et al.			03/28/88
	4,068,020	01/10/78	REUSCHEL, Konrad			12/29/75
	4,591,892	05/27/86	YAMAZAKI, Shunpei			08/22/83
	4,378,417	03/29/83	MARUYAMA et al.			04/15/81
	4,365,013	12/21/82	ISHIOKA et al.			07/28/81
	4,597,160	07/01/86	IPRI, Alfred C.			08/09/85
	5,077,223	12/31/91	YAMAZAKI, Shunpei			11/29/89
	4,888,305	12/19/89	YAMAZAKI et al.			03/09/89
	4,969,025	11/06/90	YAMAMOTO et al.			09/25/89
SWC	5,132,754	07/21/92	SERIKAWA et al.			07/21/88

FOREIGN PATENT DOCUMENTS

Document Number	Date	Country	Class	Subclass	Translation Yes No

RECEIVED

JUL 08 1998

GROUP 2100

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

SWC	PUMMER, "Commercial Excimer Lasers", Scientific and Engineering Applications of Commercial Laser Devices", pp. 38-42.
SWC	YUKI et al., "A Full-Color LCD Addressed by Poly-Si TFT's Fabricated Below 450°C", IEE Transactions on Electron Devices, Vol. 36, No. 9, pp. 1934-7.
SWC	MASUMO et al., "Low Temperature Fabrication of Poly-Si TFT by Laser Induced Crystallization of a-Si", Journal of Non-Crystalline Solids, Vol. 115, pp. 147-149.
SWC	SAMESHIMA et al., "XeCl Excimer Laser Annealing Used to Fabricate Poly-Si TFT's", Materials Research Society Symposia, Vol. 71, 1986, pp. 435-440.

Examiner

CRANE

Date Considered

9/25/98

*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Form PTO-1449
(Rev. 8-83)U.S. Department of Commerce
Patent and Trademark Office

Attorney Docket No. 0756-958

Serial No. 08/183,800

INFORMATION DISCLOSURE STATEMENT

(See several sheets if necessary)

Applicant: Shunpei YAMAZAKI

Filing Date: 01/21/94

Group: 2508

U.S. PATENT DOCUMENTS

Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date (if appropriate)
SWL	4,740,829	04/26/88	NAKAGIRI et al.			12/03/86
	4,862,237	08/29/89	MOROZUMI, Shinji			10/04/88
	5,132,821	07/21/92	NICHOLAS, Keith H.			07/26/90
	5,250,818	10/05/93	SARASWAT et al.			03/01/91
SWL	5,744,818	04/28/98	YAMAZAKI et al.			04/25/95

FOREIGN PATENT DOCUMENTS

Document Number	Date	Country	Class	Subclass	Translation	
					Yes	No

RECEIVED

JUL 08 1998

GROUP 2100

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

Examiner

CRANE

Date Considered

9/25/98

*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.